查询CMSD2004S供应商

NEW

# CMSD2004S

## HIGH VOLTAGE SWITCHING DIODE

SUPER mini

SOT-323 CASE

Central™ Semiconductor Corp.

## DESCRIPTION

The CENTRAL SEMICONDUCTOR CMSD2004S type is a silicon switching diode manufactured by the epitaxial planar process, designed for applications requiring high voltage capability.

The following configurations are available:

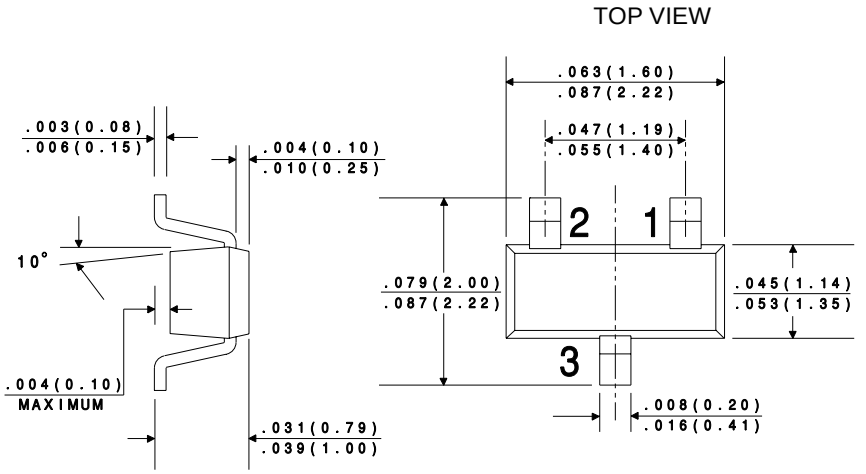
CMSD2004S DUAL, IN SERIES MARKING CODE: B6D

| **MAXIMUM RATINGS** ($T_A$=25°C) | **SYMBOL** | | **UNITS** |
|---|---|---|---|
| Continuous Reverse Voltage | $V_R$ | 240 | V |
| Peak Repetitive Reverse Voltage | $V_{RRM}$ | 300 | V |
| Peak Repetitive Reverse Current | $I_O$ | 200 | mA |
| Continuous Forward Current | $I_F$ | 225 | mA |
| Peak Repetitive Forward Current | $I_{FRM}$ | 625 | mA |
| Forward Surge Current, tp=1 μs | $I_{FSM}$ | 4000 | mA |
| Forward Surge Current, tp=1 s | $I_{FSM}$ | 1000 | mA |
| Power Dissipation | $P_D$ | 250 | mW |
| Operating and Storage Junction Temperature | $T_J$,$T_{stg}$ | -65 to +150 | °C |
| Thermal Resistance | $\Theta_{JA}$ | 500 | °C/W |

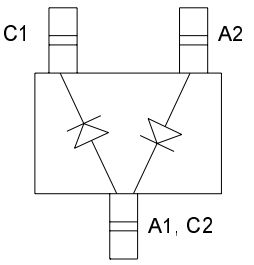
ELECTRICAL CHARACTERISTICS ($T_A$=25°C unless otherwise noted)

| **SYMBOL** | **TEST CONDITIONS** | **MIN** | **MAX** | **UNIT** |
|---|---|---|---|---|
| $BV_R$ | $I_R$=100μA | 300 | | V |
| $I_R$ | $V_R$=200V | | - | nA |
| $I_R$ | $V_R$=200V, $T_A$=150°C | | - | μA |
| $I_R$ | $V_R$=240V | | 100 | nA |
| $I_R$ | $V_R$=240V, $T_A$=150°C | | 100 | μA |
| $V_F$ | $I_F$=100mA | | 1.0 | V |
| $C_T$ | $V_R$=0, f=1 MHz | | 5.0 | pF |
| $t_{rr}$ | $I_F$=$I_R$=30mA, RECOV. TO 3.0mA,$R_L$=100Ω | | 50 | ns |

All dimensions in inches (mm).




## LEAD CODE




R3